

# 2SK1869 L, 2SK1869 S

Silicon N Channel MOS FET

## Application

High speed power switching

## Features

- Low on-resistance
- High speed switching
- Low drive current
- No Secondary Breakdown
- Suitable for Switching regulator, DC – DC converter

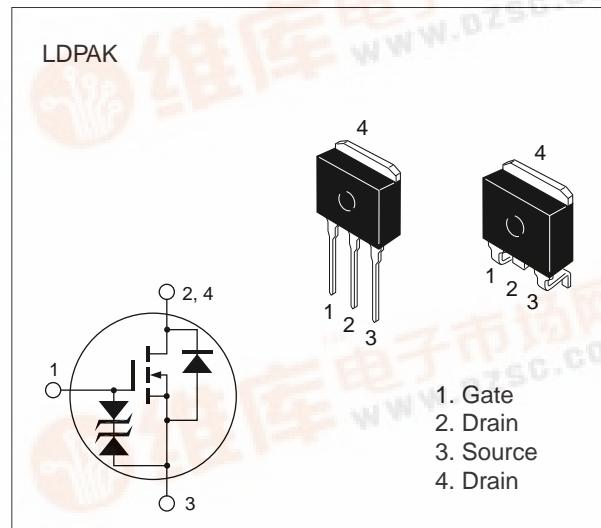


Table 1 Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	350	V
Gate to source voltage	$V_{GSS}$	$\pm 30$	V
Drain current	$I_D$	7	A
Drain peak current	$I_{D(\text{pulse})}^*$	28	A
Body-drain diode reverse drain current	$I_{DR}$	7	A
Channel dissipation	$P_{ch}^{**}$	50	W
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

\*  $PW \leq 10 \mu\text{s}$ , duty cycle  $\leq 1\%$

\*\* Value at  $T_c = 25^\circ\text{C}$

**Table 2 Electrical Characteristics (Ta = 25°C)**

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	350	—	—	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR)GSS</sub>	±30	—	—	V	I <sub>G</sub> = ±100 µA, V <sub>DS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	µA	V <sub>GS</sub> = ±25 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	250	µA	V <sub>DS</sub> = 280 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS(off)</sub>	2.0	—	3.0	V	I <sub>D</sub> = 1 mA, V <sub>DS</sub> = 10 V
Static drain to source on state resistance	R <sub>DS(on)</sub>	—	0.6	0.8	Ω	I <sub>D</sub> = 4 A V <sub>GS</sub> = 10 V *
Forward transfer admittance	y <sub>fs</sub>	3.0	5.0	—	S	I <sub>D</sub> = 4 A V <sub>DS</sub> = 10 V *
Input capacitance	C <sub>iss</sub>	—	635	—	pF	V <sub>DS</sub> = 10 V
Output capacitance	C <sub>oss</sub>	—	230	—	pF	V <sub>GS</sub> = 0
Reverse transfer capacitance	C <sub>rss</sub>	—	40	—	pF	f = 1 MHz
Turn-on delay time	t <sub>d(on)</sub>	—	10	—	ns	I <sub>D</sub> = 4 A
Rise time	t <sub>r</sub>	—	50	—	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	t <sub>d(off)</sub>	—	60	—	ns	R <sub>L</sub> = 7.5Ω
Fall time	t <sub>f</sub>	—	40	—	ns	
Body-drain diode forward voltage	V <sub>DF</sub>	—	0.95	—	V	I <sub>F</sub> = 7 A, V <sub>GS</sub> = 0
Body-drain diode reverse recovery time	t <sub>rr</sub>	—	240	—	ns	I <sub>F</sub> = 7 A, V <sub>GS</sub> = 0, diF / dt = 100 A / µs

\* Pulse Test

See characteristic curves of 2SK1400A